

Hydrogen interaction with point defects in the Si-SiO₂ structures and its influence on the interface properties

Kropman, Daniel; Mellikov, Enn; Kärner, T.; Ugaste, Ülo; Laas, Tõnu; Heinmaa, I.; Abru, Uno; Medvid, A. Solid state phenomena 2008 / p. 345-350 <https://www.scientific.net/SSP.131-133.345>

Interaction between point defects, extended defects and impurities in the Si-SiO₂ system during the process of its formation

Kropman, Daniel; Kärner, T.; Abru, Uno; Ugaste, Ülo; **Mellikov, Enn** Thin solid films 2004 / 1/2, p. 53-57 : ill <https://www.sciencedirect.com/science/article/abs/pii/S0921510704003459>

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Kas III kvartali majanduskasv valmistas teile pettumuse? : [Äripäeva küsitlusele vastavad Uno Abru, Priit Kivi, Jaak Leimann ja Veikko Maripuu]

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Point defects interaction with extended defects in the Si-SiO₂ system [Electronic resource]

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